## General purpose (dual transistors)

## FMW3 / FMW4 / IMX8

## -Features

1) Two 2SC3906K chips in an SMT package.
2) High breakdown voltage.
-Absolute maximum ratings $\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)$

| Parameter | Symbol | Limits | Unit |  |
| :---: | :---: | :---: | :---: | :---: |
| Collector-base voltage | $\mathrm{V}_{\text {cbo }}$ | 120 | V |  |
| Collector-emitter voltage | Vсео | 120 | V |  |
| Emitter-base voltage | Vebo | 5 | V |  |
| Collector current | Ic | 50 | mA |  |
| Power dissipation | Pc | 300(TOTAL) | mW | * |
| Junction temperature | Tj | 150 | ${ }^{\circ} \mathrm{C}$ |  |
| Storage temperature | Tstg | $-55 \sim+150$ | ${ }^{\circ} \mathrm{C}$ |  |

-Package, marking, and packaging specifications

| Part No. | FMW3 | FMW4 | IMX8 |
| :---: | :---: | :---: | :---: |
| Package | SMT5 | SMT5 | SMT6 |
| Marking | W3 | W4 | X4 |
| Code | T148 | T148 | T108 |
| Basic ordering unit (pieces) | 3000 | 3000 | 3000 |

-Circuit diagrams


- External dimensions (Units : mm)
FMW3
FMW4
ROHM : SMT5
EIAJ : SC-74A
-Electrical characteristics $\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)$

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-base breakdown voltage | BV сво | 120 | - | - | V | $\mathrm{Ic}=50 \mu \mathrm{~A}$ |  |
| Collector-emitter breakdown voltage | BV $\mathrm{c}_{\text {coo }}$ | 120 | - | - | V | $\mathrm{Ic}=1 \mathrm{~mA}$ |  |
| Emitter-base breakdown voltage | BVEbo | 5 | - | - | V | $\mathrm{I}=50 \mu \mathrm{~A}$ |  |
| Collector cutoff current | Icbo | - | - | 0.5 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{cb}}=100 \mathrm{~V}$ |  |
| Emitter cutoff current | Iebo | - | - | 0.5 | $\mu \mathrm{A}$ | $\mathrm{V}_{\text {Eb }}=4 \mathrm{~V}$ |  |
| DC current transfer ratio | hfe | 180 | - | 820 | - | VCE=6V, Ic=2mA |  |
| Transition frequency | ${ }_{\text {f }}$ | - | 140 | - | MHz | $\mathrm{V}_{\mathrm{CE}}=-12 \mathrm{~V}, \mathrm{I}_{\mathrm{E}=2 \mathrm{~mA}, \mathrm{f}=100 \mathrm{MHz}}$ | * |
| Collector-emitter saturation voltage | $\mathrm{V}_{\text {cE(sat) }}$ | - | - | 0.5 | V | $1 \mathrm{c} / \mathrm{lb}=10 \mathrm{~mA} / 1 \mathrm{~mA}$ |  |

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